

## N-channel TrenchMOS intermediate level FET

Rev. 1 — 12 July 2011

Product data sheet

### 1. Product profile

#### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources

#### **1.3 Applications**

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

### 1.4 Quick reference data

#### Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ [1]}$ see Figure 1	-	-	90	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	-	128	W
Static char	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	4.4	5.2	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Avalanche	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} &I_D = 90 \text{ A};  \text{V}_{sup} \leq 30  \text{V}; \\ &R_{GS} = 50  \Omega;  \text{V}_{GS} = 10  \text{V}; \\ &T_{j(\text{init})} = 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	153	mJ
Dynamic of	characteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V};$ $V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14	-	16.2	-	nC

SOT428 (DPAK)

. . . . .

[1] Continuous current is limited by package.

#### 2. **Pinning information**

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>_</u>
2	D	drain	mb	B
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

#### **Ordering information** 3.

Table 3. Ordering	g information		
Type number	Package		
	Name	Description	Version
BUK625R2-30C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	Min	Max	Unit
	-	30	V
<u>[1]</u>	-20	20	V
[2]	-16	16	V
[3]	-	90	А
1	-	81	А
	-	455	А
	-	128	W
	-55	175	°C
	-55	175	°C
[3]	-	90	А
	-	455	А
	-	153	mJ
[4][5][6	1 -	-	mJ
	[ <u>3]</u> [	3       -         -       -         <	[3]       -       90         1       -       81         -       455         -       128         -55       175         -55       175         [3]       -       90         -       455         [3]       -       90         -       153

[1] Accumulated pulse duration not to exceed 5 mins.

[2] -16V accumulated duration not to exceed 168 hrs

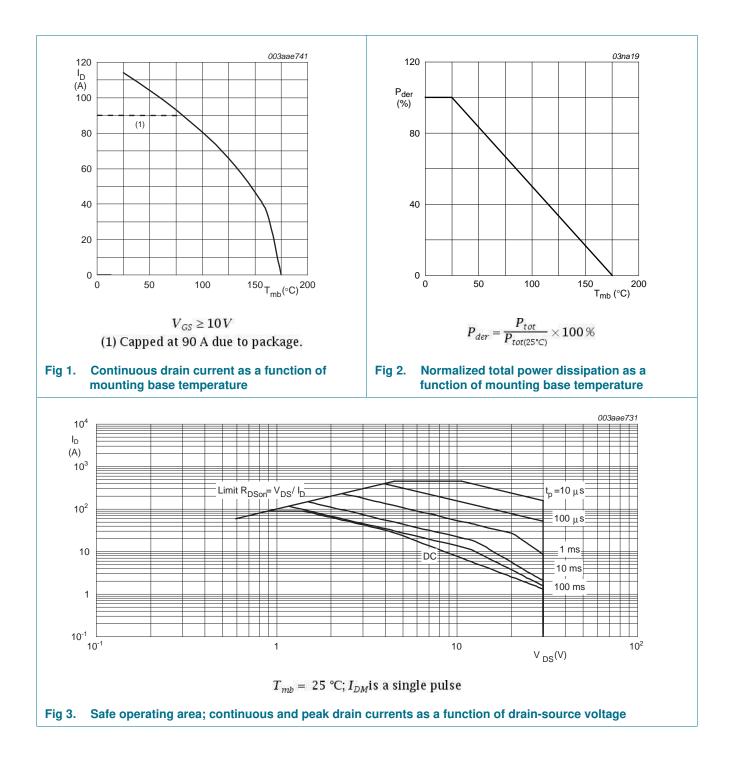
[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

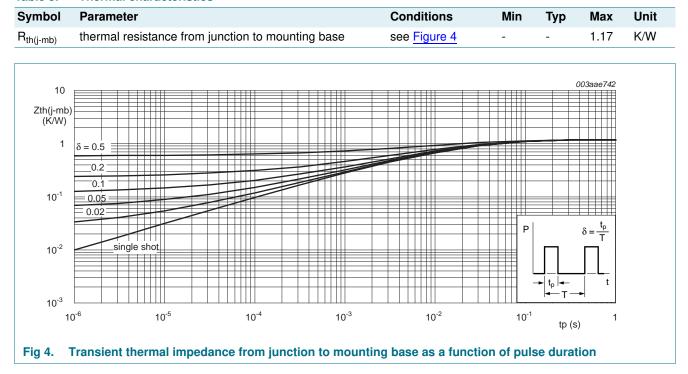
[6] Refer to application note AN10273 for further information.

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### 5. Thermal characteristics



#### Table 5. Thermal characteristics

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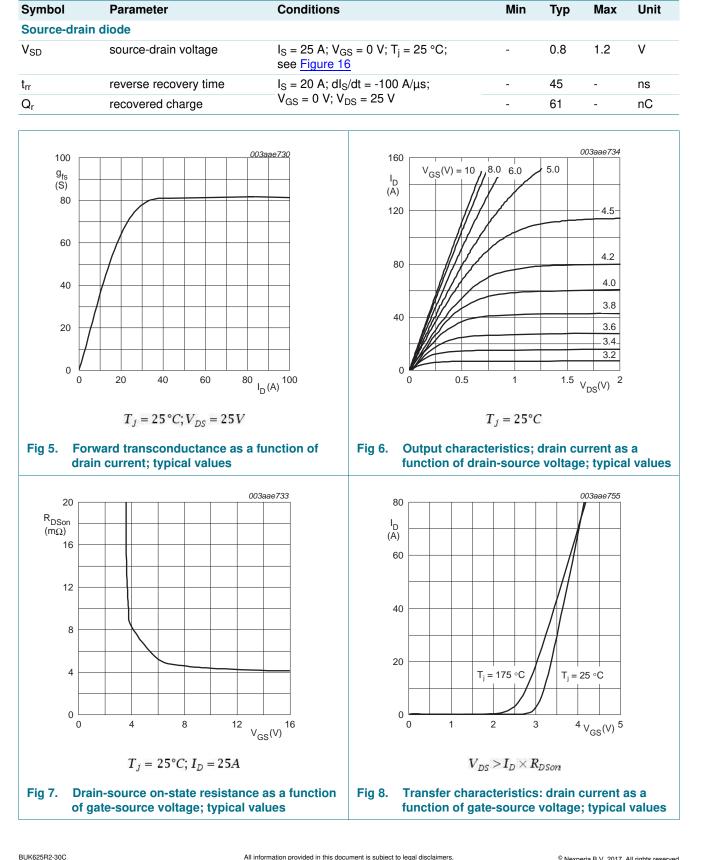
### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
(2.1)200	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$\label{eq:ID} \begin{split} I_D = 1 \mbox{ mA; } V_{DS} = V_{GS};  T_j = -55 \mbox{ °C}; \\ see  Figure \mbox{ 9} \end{split}$	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 9</u>	0.8	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 15 A; $T_{j}$ = 25 °C; see Figure 11	-	4.4	5.2	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	6	7.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	7.1	9.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	-	10	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub> to	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	54.8	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	31	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	10.2	-	nC
Q <sub>GD</sub>	gate-drain charge	see Figure 13; see Figure 14	-	16.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	2600	3470	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	484	581	pF
C <sub>rss</sub>	reverse transfer capacitance		-	288	395	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	15.3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega$	-	41	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	97	-	ns
t <sub>f</sub>	fall time		-	66	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; T <sub>i</sub> = 25 °C	-	7.5	-	nH

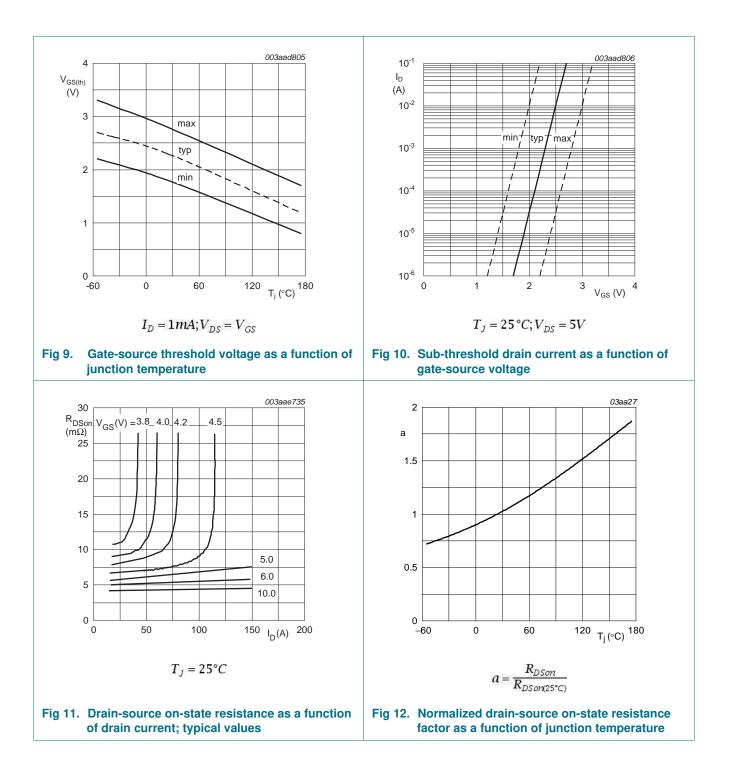
Table 6.

Characteristics ... continued

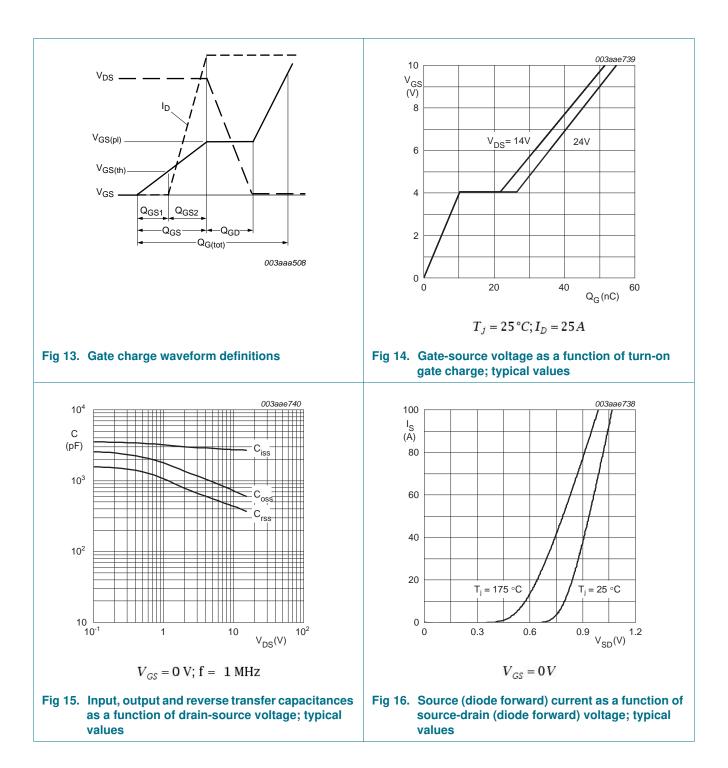
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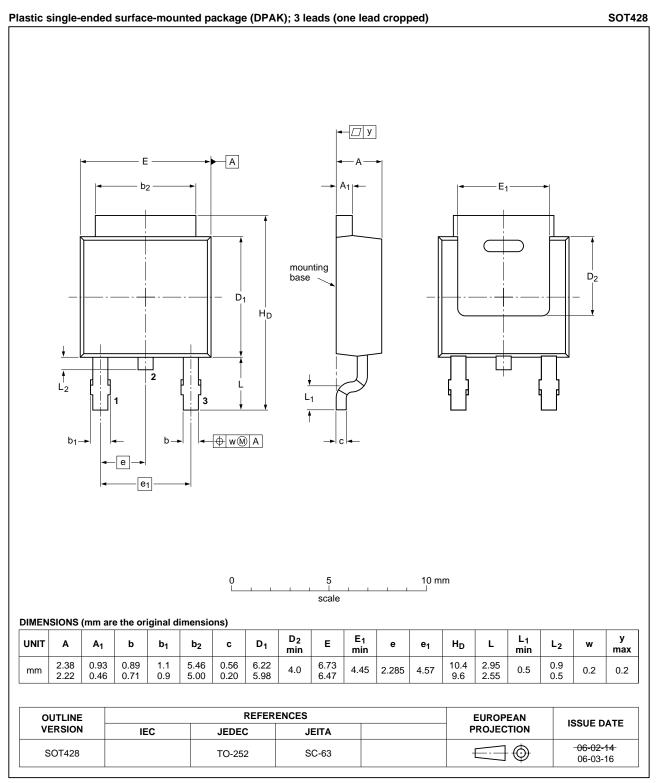


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### 7. Package outline



#### Fig 17. Package outline SOT428 (DPAK)

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### 8. Revision history

Table 7. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK625R2-30C v.1	20110712	Product data sheet	-	-

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### 9. Legal information

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Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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